

## Improved Conducting Substrate Planarization Layer for High Efficiency Flexible CIGS Photovoltaics

### **Disclosure Number**

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### **Technology Summary**

Thin film photovoltaic technology has accelerated dramatically in the past year, delivering on the promise of performance, stability and low cost. The present invention, developed under a CRADA with Global Solar provides further improvement, including provision of a low-cost, nanocrystalline planarization layer with improved barrier properties and conductivities that are suitable for supporting high efficiency, thin-film CIGS photovoltaic materials.

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